

<p>Form PTO-1449 U.S. DEPARTMENT OF COMMERCE (REV. 7-80) PATENT AND TRADEMARK OFFICE</p> <p><b>LIST OF PRIOR ART CITED BY APPLICANT</b></p> <p>(Use several sheets if necessary)</p>			Atty. Docket No. Y0R920010308US3 (16315B)		Serial N Unassigned			
			Applicant Jack O. Chu, et al.					
			Filing Date Herewith		Group Unassigned			
<b>U.S. PATENT DOCUMENTS</b>								
EXAMINER INITIAL*		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FLING DATE (if appropriate)	
<i>[initials]</i>	AA	5,906,680	5/25/1999	Meyerson				
<i>[initials]</i>	AB	6,190,975	2/2001	Kubo et al				
		2001/0160605	10/2002	Kanazawa et al.;				
		5,683,934	11/1997	Candelaria et al				
		2002/0016085	2/2002	Huang et al				
		6,306,211	10/2001	Takahashi et al.				
<b>FOREIGN PATENT DOCUMENTS</b>								
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<b>OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b>								
		E. Kasper, et al. "Growth of 100 Ghz SiGe Heterobipolar Transistor (HBT) Structures," Jpn J App Phys, Vol. 33 Pt. 1, No. 4B, April 1994, pp. 2415-2418; <i>not prior art</i> (initials) <i>or at least not in the context of this application</i>						
<i>[initials]</i>		H.J. Osten et al. "in the paper entitled "Carbon Doped SiGe Heterojunction Bipolar Transistors for High Frequency Application," IEEE BCTM 7.1, 1999, pp. 109-116;						
EXAMINER <i>J. Mondt</i>		DATE CONSIDERED <i>4/29/05</i>						
<p>* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>								